



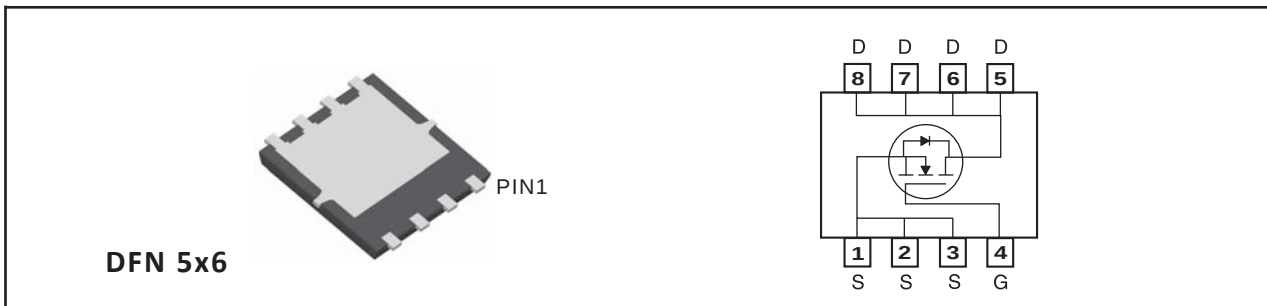
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
60V	100A	3.8 @ V _{GS} =10V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V _{DS}	Drain-Source Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
I _D	Drain Current-Continuous ^c	T _C =25°C	100	A
		T _C =70°C	80	A
I _{DM}	-Pulsed ^{a c}		203	A
E _{AS}	Single Pulse Avalanche Energy ^d		1089	mJ
P _D	Maximum Power Dissipation	T _C =25°C	83	W
		T _C =70°C	53	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	1.5	°C/W
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SP605C

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	3	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =25A		3.0	3.8	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =25A		74		S
DYNAMIC CHARACTERISTICS ^b						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		3678		pF
C _{oss}	Output Capacitance			760		pF
C _{RSS}	Reverse Transfer Capacitance			514		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		105		ns
t _r	Rise Time			183		ns
t _{D(OFF)}	Turn-Off Delay Time			115		ns
t _f	Fall Time			55		ns
Q _g	Total Gate Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		61		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		8		nC
Q _{gd}	Gate-Drain Charge			28.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =16A		0.75	1.3	V
Notes						
a. Pulse Test: Pulse Width ≤ 10us, Duty Cycle ≤ 1%.						
b. Guaranteed by design, not subject to production testing.						
c. Drain current limited by maximum junction temperature.						
d. Starting T _J =25°C, L=0.5mH, V _{DD} = 30V. (See Figure13)						
e. Mounted on FR4 Board of 1 inch ² , 2oz.						

Dec,09,2015

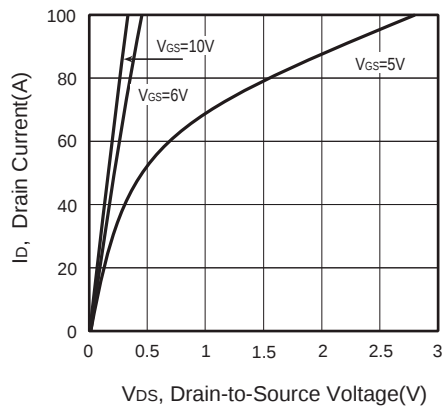


Figure 1. Output Characteristics

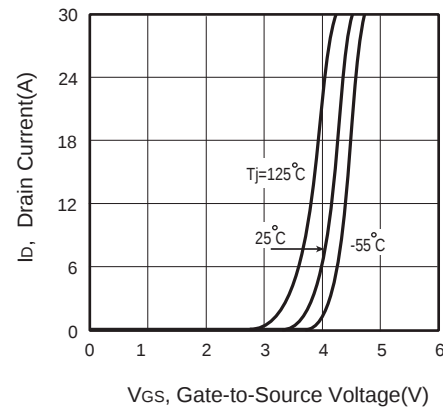


Figure 2. Transfer Characteristics

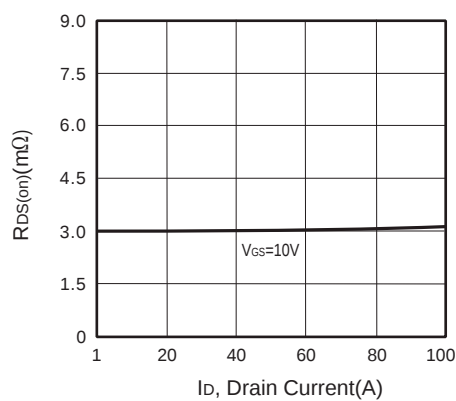


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

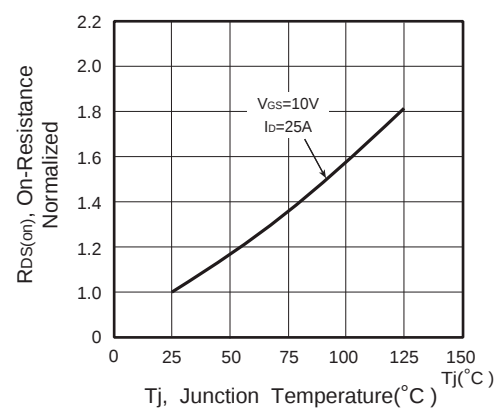


Figure 4. On-Resistance Variation with Drain Current and Temperature

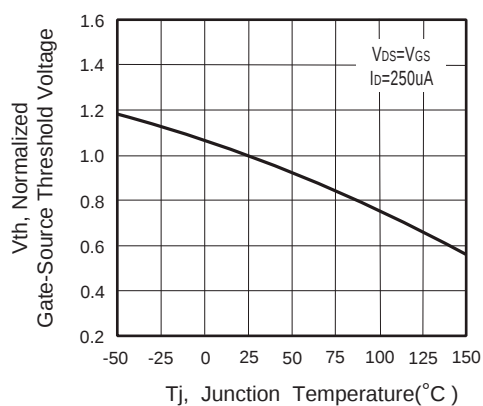


Figure 5. Gate Threshold Variation with Temperature

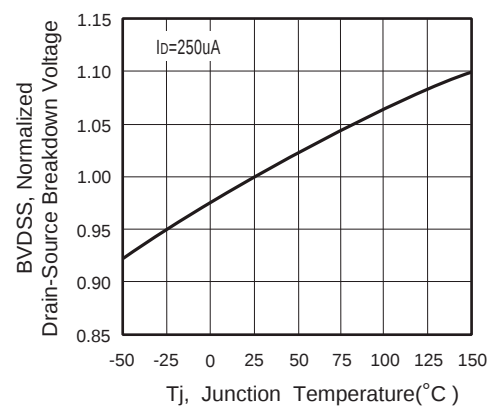
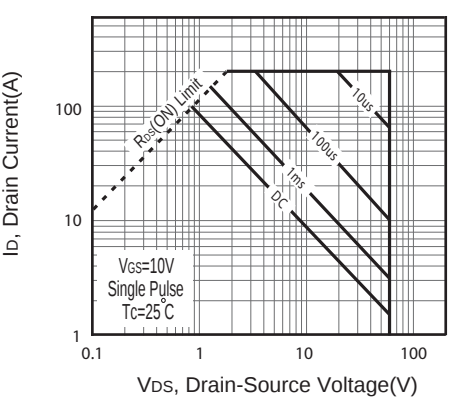
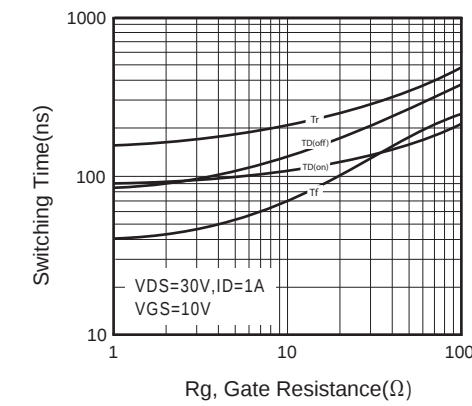
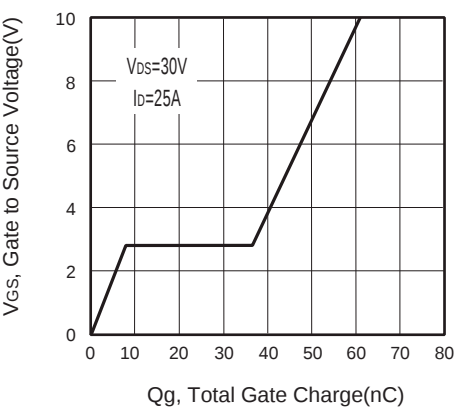
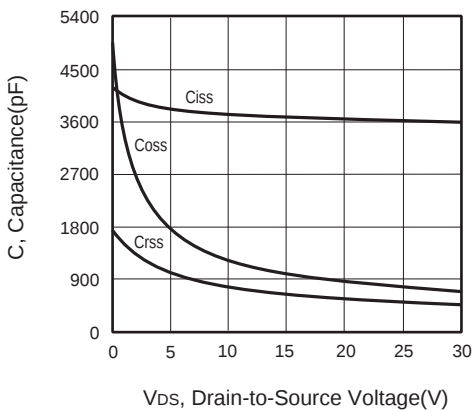
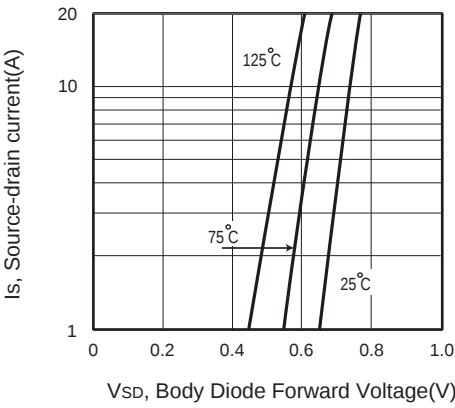
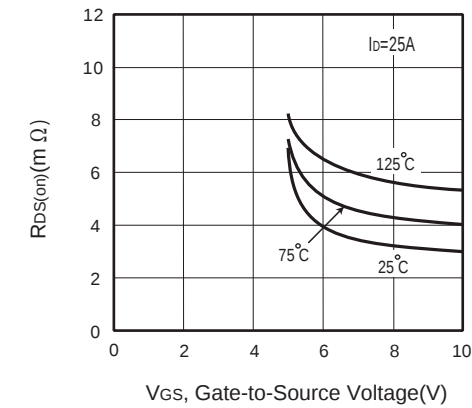
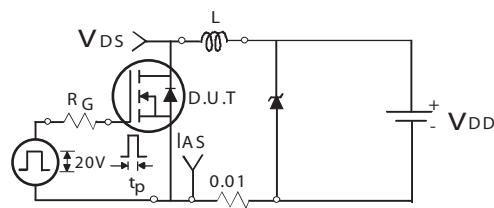


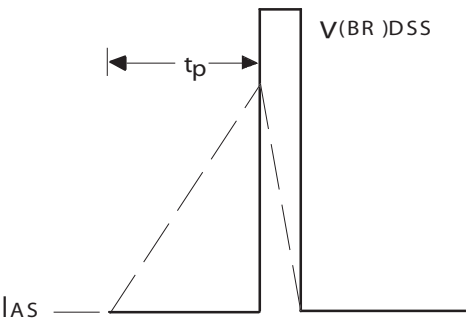
Figure 6. Breakdown Voltage Variation with Temperature





Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

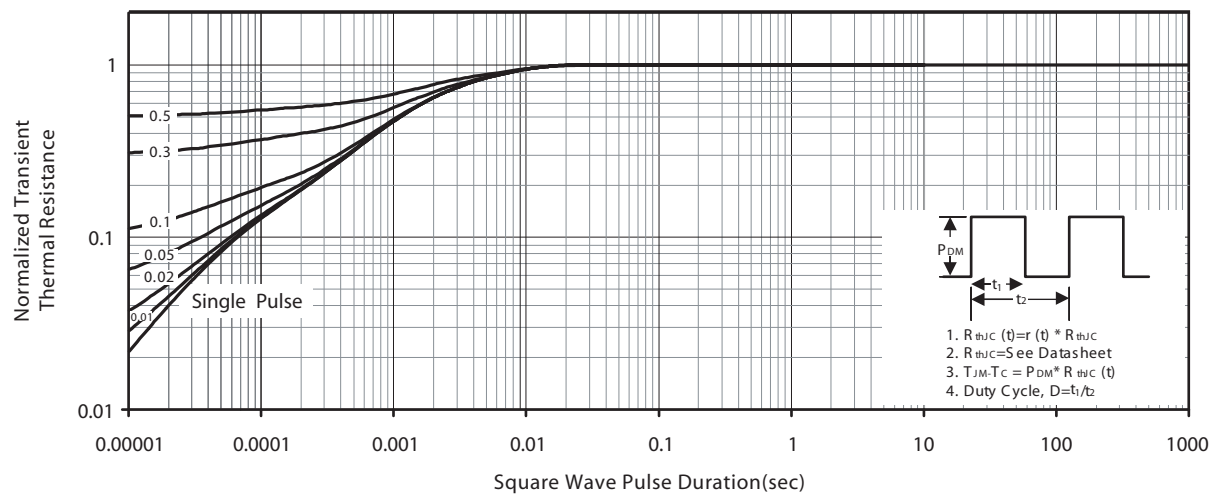
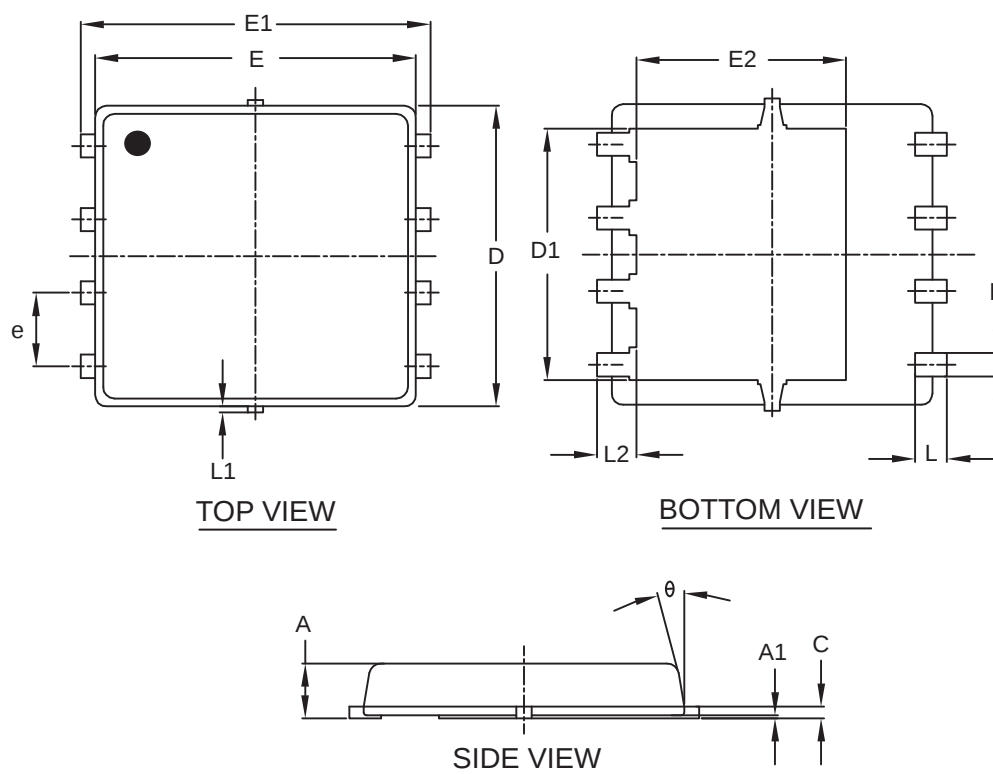


Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

DFN 5x6-8L



SYMBOLS	MILLIMETERS		
	MIN	NOM	MAX
A	0.85	0.95	1.00
A1	0.00	—	0.05
b	0.30	0.40	0.50
c	0.15	0.20	0.25
D	5.20 BSC		
D1	4.35 BSC		
E	5.55 BSC		
E1	6.05 BSC		
E2	3.62 BSC		
e	1.27 BSC		
L	0.45	0.55	0.65
L1	0.00	—	0.15
L2	0.68 REF		
θ	0°	—	10°

TOP MARKING DEFINITION

